



# M48Z512A M48Z512AY, M48Z512AV

## 4 Mbit (512Kb x8) ZEROPOWER® SRAM

- INTEGRATED LOW POWER SRAM, POWER-FAIL CONTROL CIRCUIT and BATTERY
- CONVENTIONAL SRAM OPERATION; UNLIMITED WRITE CYCLES
- 10 YEARS of DATA RETENTION in the ABSENCE of POWER
- AUTOMATIC POWER-FAIL CHIP DESELECT and WRITE PROTECTION
- WRITE PROTECT VOLTAGES ( $V_{PFD}$  = Power-fail Deselect Voltage):
  - M48Z512A:  $4.50V \leq V_{PFD} \leq 4.75V$
  - M48Z512AY:  $4.20V \leq V_{PFD} \leq 4.50V$
  - M48Z512AV:  $2.80V \leq V_{PFD} \leq 3.00V$
- BATTERY INTERNALLY ISOLATED UNTIL POWER IS APPLIED
- PIN and FUNCTION COMPATIBLE with JEDEC STANDARD 512K x 8 SRAMs
- SURFACE MOUNT CHIP SET PACKAGING INCLUDES a 28-PIN SOIC and a 32-LEAD TSOP (SNAPHAT TOP TO BE ORDERED SEPARATELY)
- SOIC PACKAGE PROVIDES DIRECT CONNECTION for a SNAPHAT TOP WHICH CONTAINS the BATTERY
- SNAPHAT® HOUSING (BATTERY) IS REPLACEABLE

### DESCRIPTION

The M48Z512A/512AY/512AV ZEROPOWER® RAM is a non-volatile 4,194,304 bit Static RAM organized as 524,288 words by 8 bits. The device combines an internal lithium battery, a CMOS SRAM and a control circuit in a plastic 32 pin DIP Module.

For surface mount environments ST provides a Chip Set solution consisting of a 28 pin 330mil SOIC NVRAM Supervisor (M40Z300/W) and a 32 pin TSOP Type II (10 x 20mm) LPSRAM (M68Z512/W) packages. Both 5V and 3V versions are available (see Table 5).

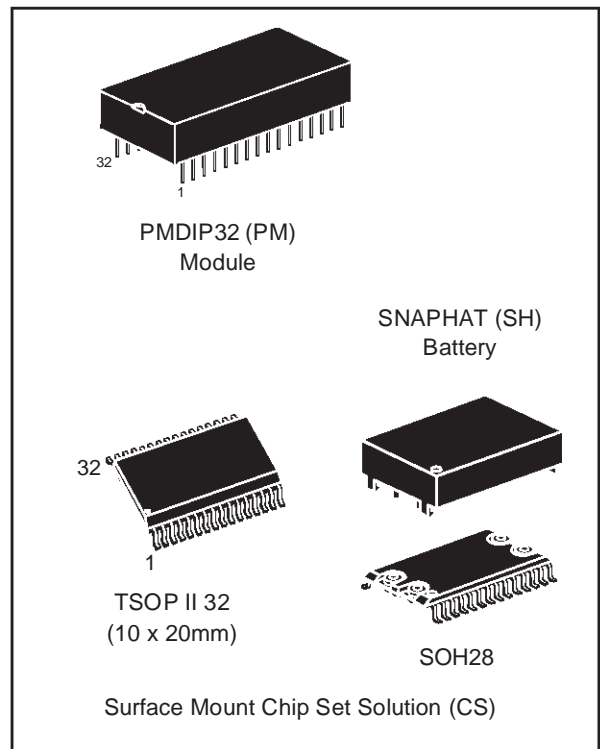


Figure 1. Logic Diagram

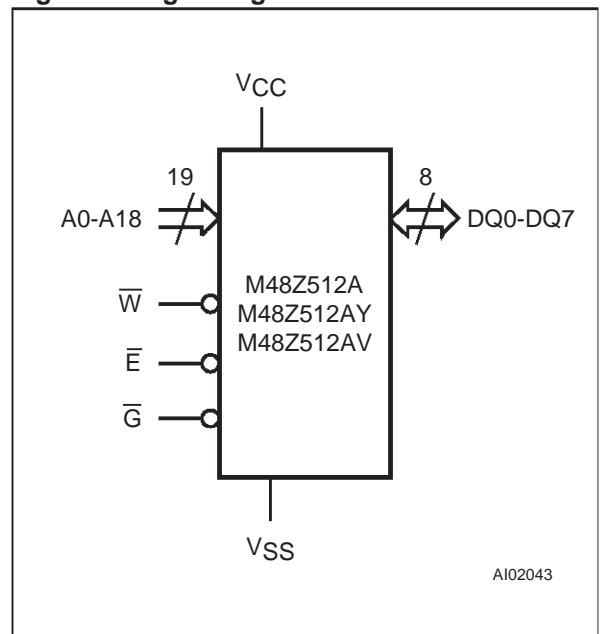
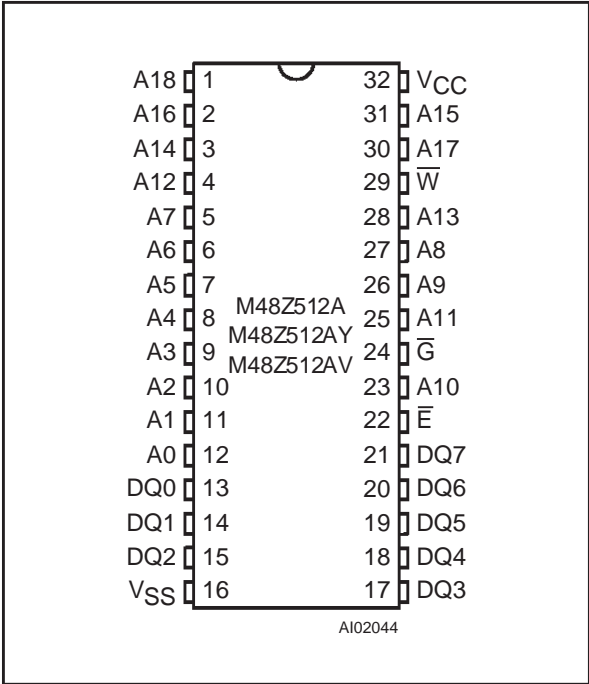


Figure 2. DIP Connections



The unique design allows the SNAPHAT battery package to be mounted on top of the SOIC package after the completion of the surface mount process. Insertion of the SNAPHAT housing after reflow prevents potential battery damage due to the high temperatures required for device surface-mounting. The SNAPHAT housing is keyed to prevent reverse insertion.

Table 1. Signal Names

A0-A18	Address Inputs
DQ0-DQ7	Data Inputs / Outputs
$\overline{E}$	Chip Enable
$\overline{G}$	Output Enable
$\overline{W}$	Write Enable
VCC	Supply Voltage
VSS	Ground

The SNAPHAT battery package is shipped separately in plastic anti-static tubes or in Tape & Reel form. The part number is "M4Z32-BR00SH1".

The M48Z512A/512AY/512AV also has its own Power-fail Detect circuit. The control circuitry constantly monitors the single VCC supply for an out of tolerance condition. When VCC is out of tolerance, the circuit write protects the SRAM, providing a high degree of data security in the midst of unpredictable system operation brought on by low VCC. As VCC falls below the switchover voltage (VSO), the control circuitry connects the battery which maintains data until valid power returns.

The ZEROPOWER RAM replaces industry standard SRAMs. It provides the nonvolatility of PROMs without any requirement for special write timing or limitations on the number of writes that can be performed.

Table 2. Absolute Maximum Ratings <sup>(1)</sup>

Symbol	Parameter	Value	Unit
T <sub>A</sub>	Ambient Operating Temperature	0 to 70	°C
T <sub>STG</sub>	Storage Temperature (V <sub>CC</sub> Off)	–40 to 70	°C
T <sub>BIAS</sub>	Temperature Under Bias	–40 to 70	°C
T <sub>SLD</sub> <sup>(2)</sup>	Lead Solder Temperature for 10 seconds	260	°C
V <sub>IO</sub>	Input or Output Voltages	–0.3 to 7	V
V <sub>CC</sub>	Supply Voltage	M48Z512A/AY	V
		M48Z512AV	

Note: 1. Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to the absolute maximum rating conditions for extended periods of time may affect reliability.

2. Soldering temperature not to exceed 260°C for 10 seconds (total thermal budget not to exceed 150°C for longer than 30 seconds).

**CAUTION:** Negative undershoots below –0.3V are not allowed on any pin while in the Battery Back-up mode.

Table 3. Operating Modes

Mode	V <sub>CC</sub>	$\overline{E}$	$\overline{G}$	$\overline{W}$	DQ0-DQ7	Power
Deselect	4.75V to 5.5V or 4.5V to 5.5V or 3.0V to 3.6V	V <sub>IH</sub>	X	X	High Z	Standby
Write		V <sub>IL</sub>	X	V <sub>IL</sub>	D <sub>IN</sub>	Active
Read		V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	D <sub>OUT</sub>	Active
Read		V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IH</sub>	High Z	Active
Deselect	V <sub>SO</sub> to V <sub>PFD</sub> (min)	X	X	X	High Z	CMOS Standby
Deselect	≤ V <sub>SO</sub>	X	X	X	High Z	Battery Back-up Mode

Note: 1. X = V<sub>IH</sub> or V<sub>IL</sub>; V<sub>SO</sub> = Battery Back-up Switchover Voltage.

Figure 3. Block Diagram

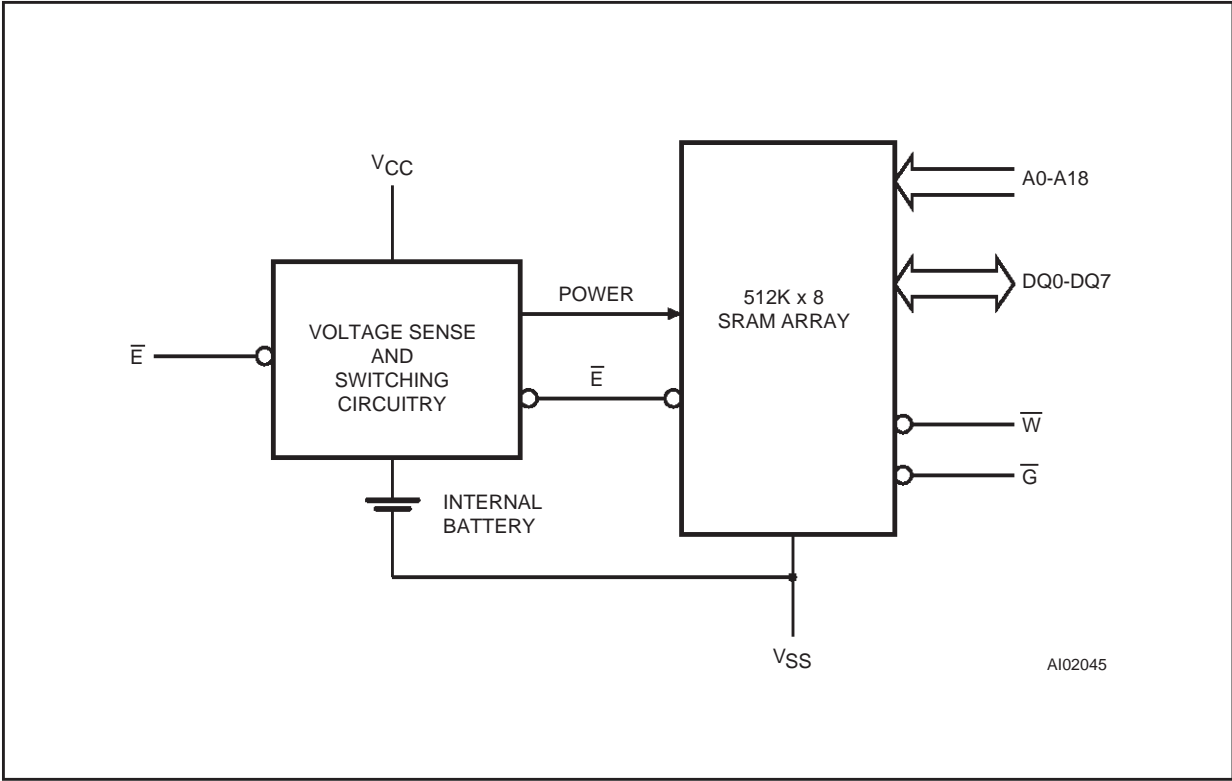
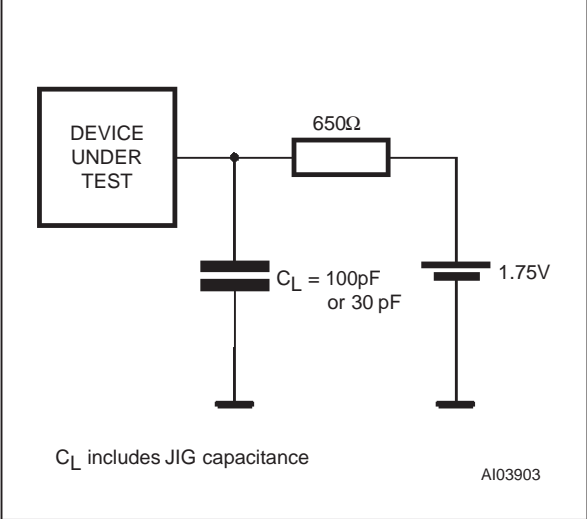


Table 4. AC Measurement Conditions

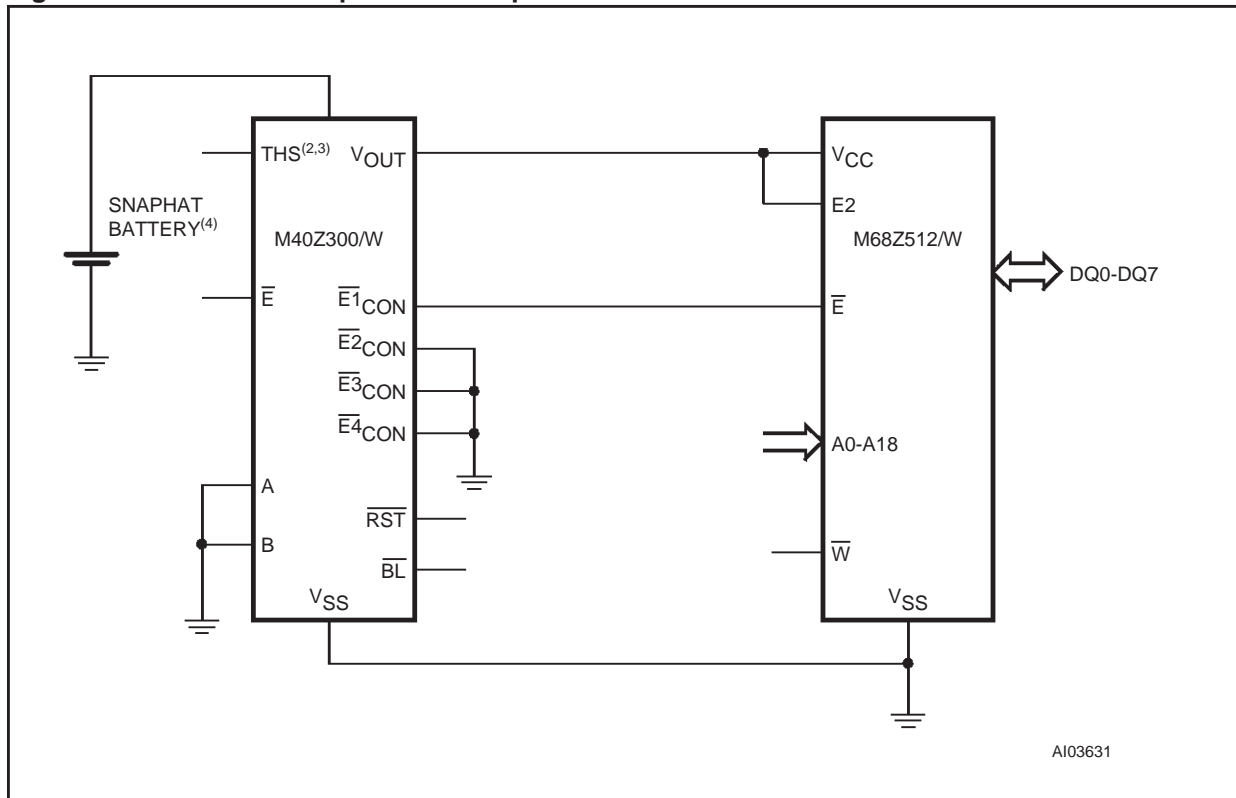
Input Rise and Fall Times	$\leq 5\text{ns}$
Input Pulse Voltages	0 to 3V
Input and Output Timing Ref. Voltages	1.5V

Note that Output Hi-Z is defined as the point where data is no longer driven.

Figure 4. AC Testing Load Circuit



Note: Excluding open drain output pins.

Figure 5. Hardware Hookup for SMT Chip Set <sup>(1)</sup>

Note: 1. For pin connections, see individual data sheets for M40Z300/W and M68Z512/W at [www.st.com](http://www.st.com).  
 2. Connect THS pin to V<sub>OUT</sub> if  $4.2V \leq V_{PFD} \leq 4.5V$  (M48Z512AY) or connect THS pin to V<sub>SS</sub> if  $4.5V \leq V_{PFD} \leq 4.75V$  (M48Z512A).  
 3. Connect THS pin to V<sub>SS</sub> if  $2.8V \leq V_{PFD} \leq 3.0V$  (M48Z512AV).  
 4. SNAPHAT top ordered separately.

Table 5. ChipSet Solution

NVRAM	LPSRAM	SUPERVISOR	THS Pin <sup>(1)</sup>
M48Z512A	M68Z128	M40Z300	V <sub>SS</sub>
M48Z512AY	M68Z128	M40Z300	V <sub>OUT</sub>
M48Z512AV	M68Z128W	M40Z300W	V <sub>SS</sub>

Note: 1. Connection of Threshold Select Pin (Pin 13) of SUPERVISOR (M40Z300/W).

**M48Z512A, M48Z512AY, M48Z512AV****Table 6. Capacitance (1, 2)**(T<sub>A</sub> = 25 °C, f = 1MHz)

Symbol	Parameter	Test Condition	Min	Max	Unit
C <sub>IN</sub>	Input Capacitance	V <sub>IN</sub> = 0V		10	pF
C <sub>IO</sub> <sup>(3)</sup>	Input / Output Capacitance	V <sub>OUT</sub> = 0V		10	pF

Note: 1. Effective capacitance measured with power supply at 5V.

2. Sampled only, not 100% tested.

3. Outputs deselected.

**Table 7A. DC Characteristics**(T<sub>A</sub> = 0 to 70 °C; V<sub>CC</sub> = 4.75V to 5.5V or 4.5V to 5.5V)

Symbol	Parameter	Test Condition	Min	Max	Unit
I <sub>LI</sub> <sup>(1)</sup>	Input Leakage Current	0V ≤ V <sub>IN</sub> ≤ V <sub>CC</sub>		±1	μA
I <sub>LO</sub> <sup>(1)</sup>	Output Leakage Current	0V ≤ V <sub>OUT</sub> ≤ V <sub>CC</sub>		±1	μA
I <sub>CC</sub>	Supply Current	$\bar{E} = V_{IL}$ , Outputs open		115	mA
I <sub>CC1</sub>	Supply Current (Standby) TTL	$\bar{E} = V_{IH}$		10	mA
I <sub>CC2</sub>	Supply Current (Standby) CMOS	$\bar{E} \geq V_{CC} - 0.2V$		5	mA
V <sub>IL</sub>	Input Low Voltage		-0.3	0.8	V
V <sub>IH</sub>	Input High Voltage		2.2	V <sub>CC</sub> + 0.3	V
V <sub>OL</sub>	Output Low Voltage	I <sub>OL</sub> = 2.1mA		0.4	V
V <sub>OH</sub>	Output High Voltage	I <sub>OH</sub> = -1mA	2.4		V

Note: 1. Outputs deselected.

**Table 7B. DC Characteristics**(T<sub>A</sub> = 0 to 70 °C; V<sub>CC</sub> = 3.0V to 3.6V)

Symbol	Parameter	Test Condition	Min	Max	Unit
I <sub>LI</sub> <sup>(1)</sup>	Input Leakage Current	0V ≤ V <sub>IN</sub> ≤ V <sub>CC</sub>		±1	μA
I <sub>LO</sub> <sup>(1)</sup>	Output Leakage Current	0V ≤ V <sub>OUT</sub> ≤ V <sub>CC</sub>		±1	μA
I <sub>CC</sub>	Supply Current	$\bar{E} = V_{IL}$ , Outputs open		50	mA
I <sub>CC1</sub>	Supply Current (Standby) TTL	$\bar{E} = V_{IH}$		4	mA
I <sub>CC2</sub>	Supply Current (Standby) CMOS	$\bar{E} \geq V_{CC} - 0.2V$		3	mA
V <sub>IL</sub>	Input Low Voltage		-0.3	0.6	V
V <sub>IH</sub>	Input High Voltage		2.2	V <sub>CC</sub> + 0.3	V
V <sub>OL</sub>	Output Low Voltage	I <sub>OL</sub> = 2.1mA		0.4	V
V <sub>OH</sub>	Output High Voltage	I <sub>OH</sub> = -1mA	2.2		V

Note: 1. Outputs deselected.

**Table 8. Power Down/Up Trip Points DC Characteristics <sup>(1)</sup>**  
 $(T_A = 0 \text{ to } 70 \text{ }^{\circ}\text{C})$

Symbol	Parameter		Min	Typ	Max	Unit
V <sub>PFD</sub>	Power-fail Deselect Voltage	M48Z512A	4.5	4.6	4.75	V
		M48Z512AY	4.2	4.3	4.5	V
		M48Z512AV	2.8	2.9	3.0	V
V <sub>SO</sub>	Battery Back-up Switchover Voltage	M48Z512A/Y		3		V
		M48Z512AV		2.5		
t <sub>DR</sub> <sup>(2)</sup>	Data Retention Time		10			YEARS

Note: 1. All voltages referenced to  $V_{SS}$ .

2. At 25 °C.

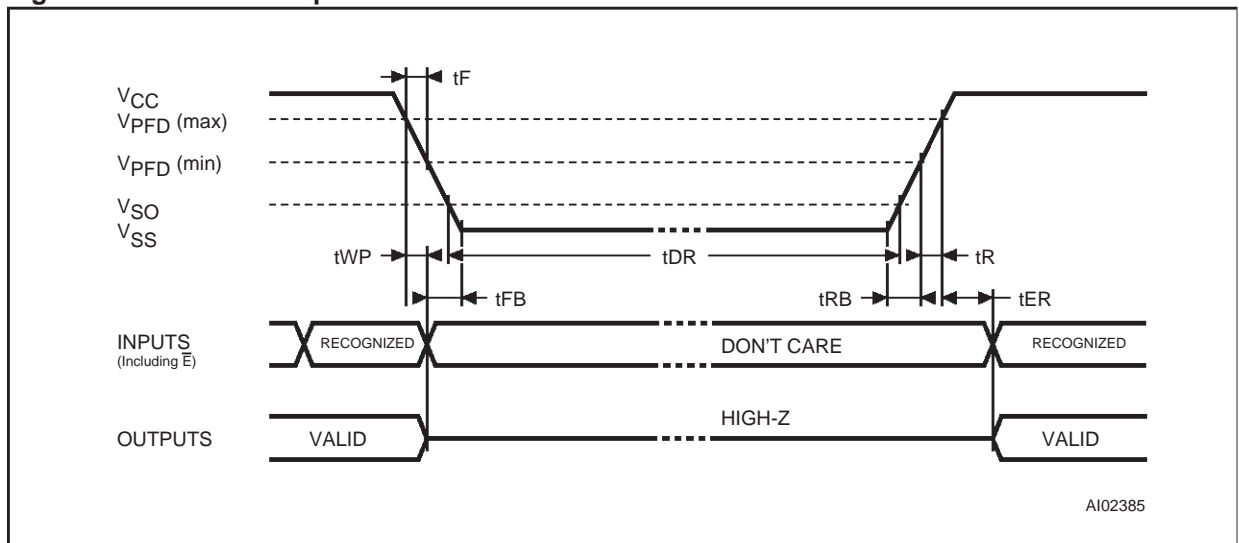
**Table 9. Power Down/Up AC Characteristics**  
 $(T_A = 0 \text{ to } 70 \text{ }^{\circ}\text{C})$

Symbol	Parameter	Min	Max	Unit
$t_F^{(1)}$	$V_{PFD}(\text{max})$ to $V_{PFD}(\text{min})$ $V_{CC}$ Fall Time	300		$\mu\text{s}$
$t_{FB}^{(2)}$	$V_{PFD}(\text{min})$ to $V_{SS}$ $V_{CC}$ Fall Time (M48Z512A/Y)	10		$\mu\text{s}$
	$V_{PFD}(\text{min})$ to $V_{SS}$ $V_{CC}$ Fall Time (M48Z512V)	150		
$t_R$	$V_{PFD}(\text{min})$ to $V_{PFD}(\text{max})$ $V_{CC}$ Rise Time	10		$\mu\text{s}$
$t_{RB}$	$V_{SS}$ to $V_{PFD}(\text{min})$ $V_{CC}$ Rise Time	1		$\mu\text{s}$
$t_{WP}$	Write Protect Time (M48Z512A/Y)	40	150	$\mu\text{s}$
	Write Protect Time (M48Z512AV)	40	250	
$t_{ER}$	$\bar{E}$ Recovery Time	40	120	ms

Note: 1.  $V_{PFD}(\text{max})$  to  $V_{PFD}(\text{min})$  fall time of less than  $t_F$  may result in deselection/write protection not occurring until 200 $\mu\text{s}$  after  $V_{CC}$  passes  $V_{PFD}(\text{min})$ .

2.  $V_{PFD}(\text{min})$  to  $V_{SS}$  fall time of less than  $t_{FB}$  may cause corruption of RAM data.

**Figure 6. Power Down/Up Mode AC Waveforms**



## M48Z512A, M48Z512AY, M48Z512AV

**Table 10. Read Mode AC Characteristics**

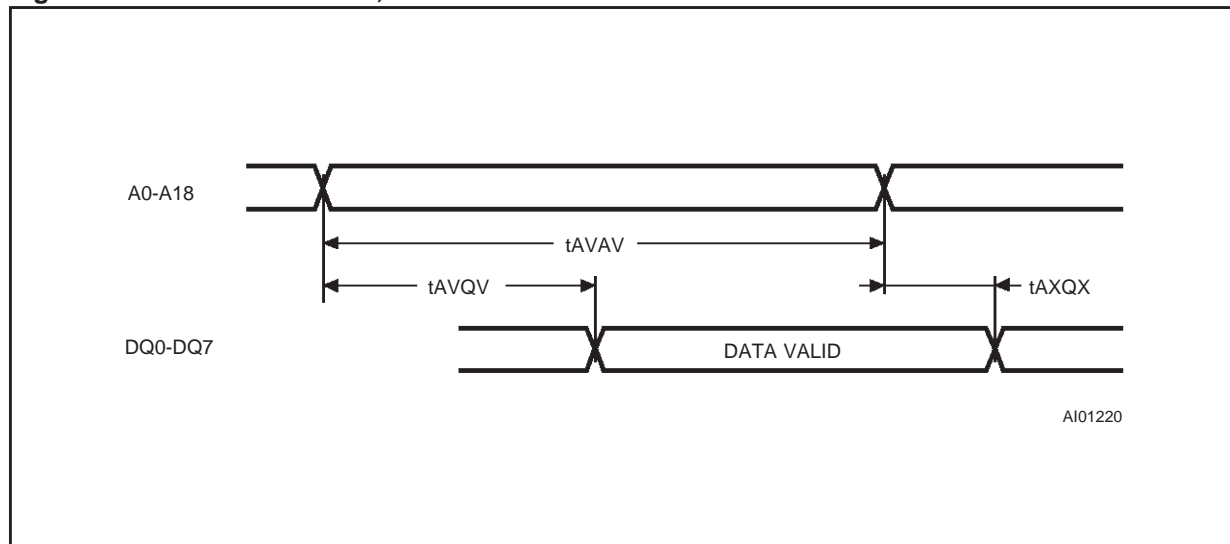
( $T_A = 0$  to  $70\text{ }^{\circ}\text{C}$ ;  $V_{CC} = 4.75\text{V}$  to  $5.5\text{V}$  or  $4.5\text{V}$  to  $5.5\text{V}$  or  $3.0\text{V}$  to  $3.6\text{V}$ )

Symbol	Parameter	M48Z512A M48Z512AY		M48Z512A M48Z512AY M48Z512AV		Unit
		-70		-85		
		Min	Max	Min	Max	
tAVAV	Read Cycle Time	70		85		ns
tAVQV <sup>(1)</sup>	Address Valid to Output Valid		70		85	ns
tELQV <sup>(1)</sup>	Chip Enable Low to Output Valid		70		85	ns
tGLQV <sup>(1)</sup>	Output Enable Low to Output Valid		35		45	ns
tELQX <sup>(2)</sup>	Chip Enable Low to Output Transition	5		5		ns
tGLQX <sup>(2)</sup>	Output Enable Low to Output Transition	5		5		ns
tEHQZ <sup>(2)</sup>	Chip Enable High to Output Hi-Z		30		35	ns
tGHQZ <sup>(2)</sup>	Output Enable High to Output Hi-Z		20		25	ns
tAXQX <sup>(1)</sup>	Address Transition to Output Transition	5		5		ns

Note: 1.  $C_L = 100\text{pF}$ .

2.  $C_L = 5\text{pF}$ .

**Figure 7. Address Controlled, Read Mode AC Waveforms**



Note: Chip Enable ( $\overline{E}$ ) and Output Enable ( $\overline{G}$ ) = Low, Write Enable ( $\overline{W}$ ) = High.





**Table 11. Write Mode AC Characteristics**
 $(T_A = 0 \text{ to } 70 \text{ }^\circ\text{C}; V_{CC} = 4.75\text{V to } 5.5\text{V or } 4.5\text{V to } 5.5\text{V or } 3.0\text{V to } 3.6\text{V})$ 

Symbol	Parameter	M48Z512A M48Z512AY		M48Z512A M48Z512AY M48Z512AV		Unit
		-70		-85		
		Min	Max	Min	Max	
tAVAV	Write Cycle Time	70		85		ns
tAVWL	Address Valid to Write Enable Low	0		0		ns
tAVEL	Address Valid to Chip Enable Low	0		0		ns
tWLWH	Write Enable Pulse Width	55		65		ns
tELEH	Chip Enable Low to Chip Enable High	55		75		ns
tWHAX	Write Enable High to Address Transition	5		5		ns
tEHAX	Chip Enable High to Address Transition	15		15		ns
tDVWH	Input Valid to Write Enable High	30		35		ns
tDVEH	Input Valid to Chip Enable High	30		35		ns
tWHDX	Write Enable High to Input Transition	0		0		ns
tEHDX	Chip Enable High to Input Transition	10		10		ns
tWLQZ <sup>(1, 2)</sup>	Write Enable Low to Output Hi-Z		25		30	ns
tAVWH	Address Valid to Write Enable High	65		75		ns
tAVEH	Address Valid to Chip Enable High	65		75		ns
tWHQX <sup>(1, 2)</sup>	Write Enable High to Output Transition	5		5		ns

Note: 1.  $C_L = 5\text{pF}$ .

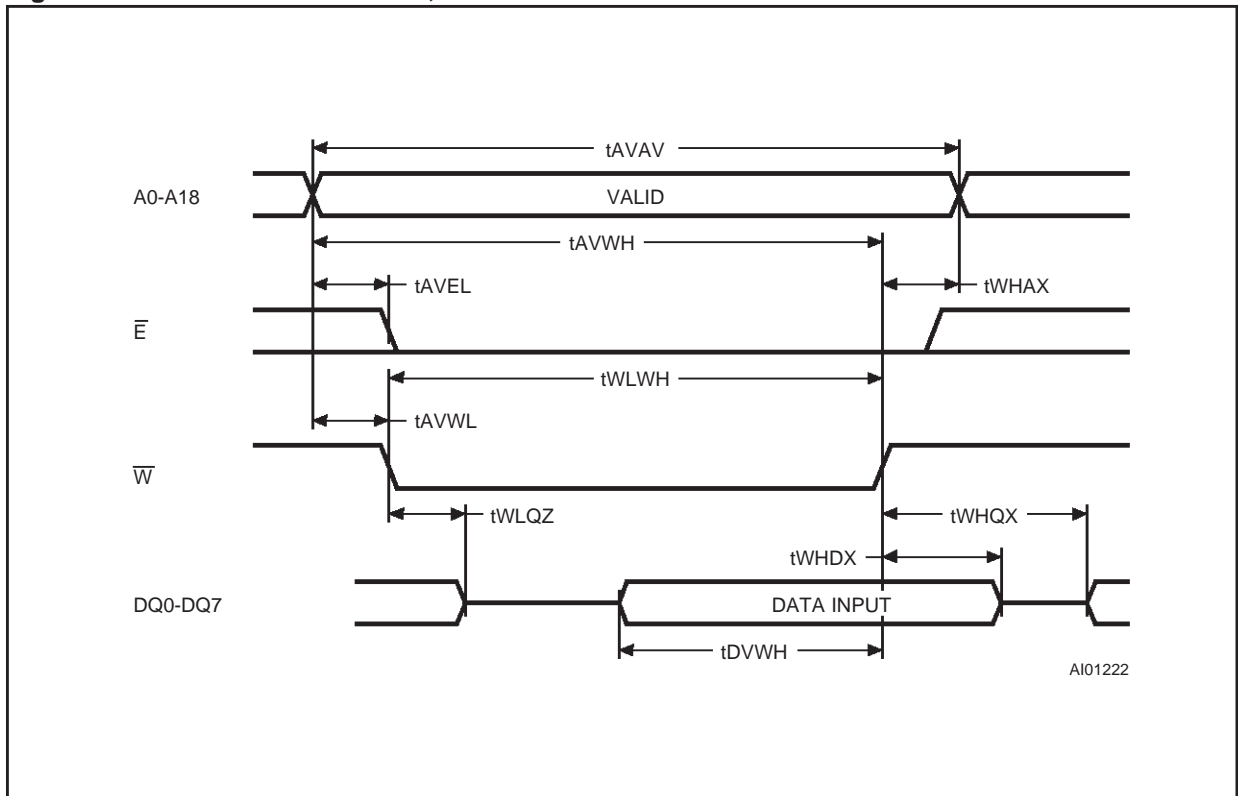
2. If  $\overline{E}$  goes low simultaneously with  $\overline{W}$  going low, the outputs remain in the high impedance state.

## WRITE MODE

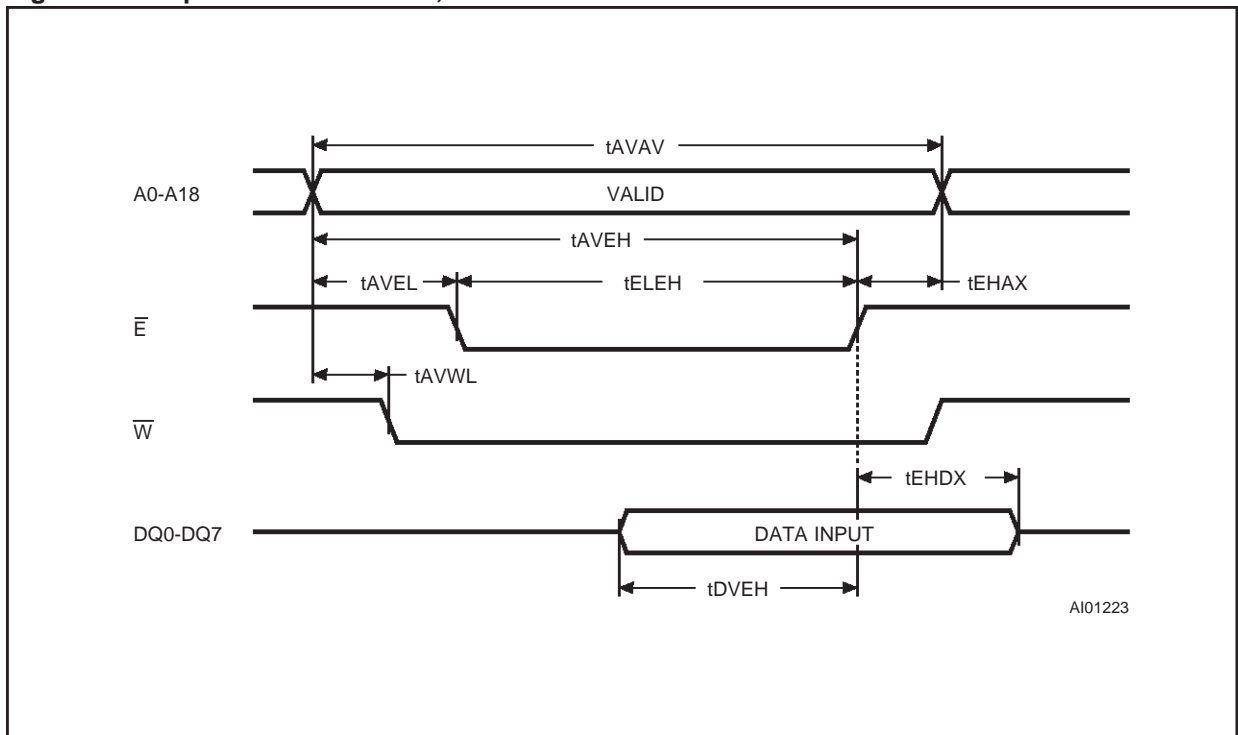
The M48Z512A/512AY/512AV is in the Write Mode whenever  $\overline{W}$  and  $\overline{E}$  are active. The start of a write is referenced from the latter occurring falling edge of  $\overline{W}$  or  $\overline{E}$ . A write is terminated by the earlier rising edge of  $\overline{W}$  or  $\overline{E}$ .

The addresses must be held valid throughout the cycle.  $\overline{E}$  or  $\overline{W}$  must return high for a minimum of  $t_E$ .

$H_{AX}$  from  $\overline{E}$  or  $t_{WHAX}$  from  $\overline{W}$  prior to the initiation of another read or write cycle. Data-in must be valid  $t_{DVEH}$  or  $t_{DVWH}$  prior to the end of write and remain valid for  $t_{EHDX}$  or  $t_{WHDX}$  afterward.  $\overline{G}$  should be kept high during write cycles to avoid bus contention; although, if the output bus has been activated by a low on  $\overline{E}$  and  $\overline{G}$ , a low on  $\overline{W}$  will disable the outputs  $t_{WLQZ}$  after  $\overline{W}$  falls.

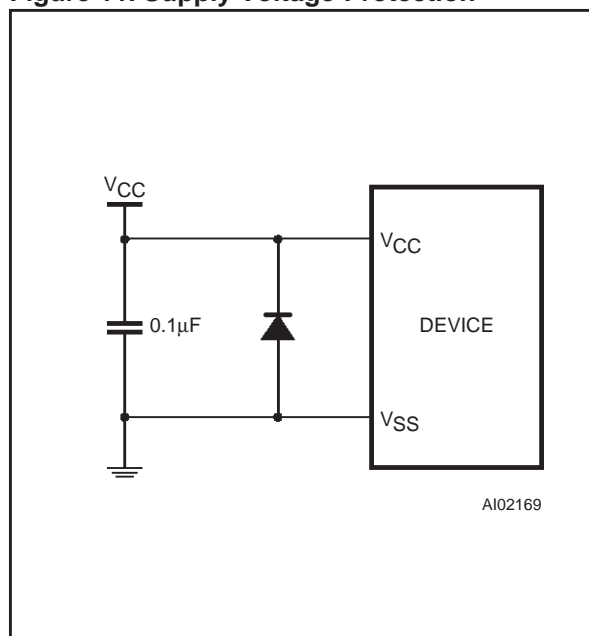
**Figure 9. Write Enable Controlled, Write AC Waveforms**

Note: Output Enable ( $\overline{G}$ ) = High.

**Figure 10. Chip Enable Controlled, Write AC Waveforms**

Note: Output Enable ( $\overline{G}$ ) = High.

Figure 11. Supply Voltage Protection



### DATA RETENTION MODE

With valid  $V_{CC}$  applied, the M48Z512A/512AY/512AV operates as a conventional BYTEWIDE™ static RAM. Should the supply voltage decay, the RAM will automatically power-fail deselect, write protecting itself  $t_{WP}$  after  $V_{CC}$  falls below  $V_{PFD}$ . All outputs become high impedance, and all inputs are treated as "don't care."

If power fail detection occurs during a valid access, the memory cycle continues to completion. If the memory cycle fails to terminate within the time  $t_{WP}$ , write protection takes place. When  $V_{CC}$  drops below  $V_{SO}$ , the control circuit switches power to the internal energy source which preserves data.

The internal coin cell will maintain data in the M48Z512A/512AY/512AV after the initial application of  $V_{CC}$  for an accumulated period of at least 10 years when  $V_{CC}$  is less than  $V_{SO}$ . As system power returns and  $V_{CC}$  rises above  $V_{SO}$ , the battery is disconnected, and the power supply is switched to external  $V_{CC}$ . Write protection continues for  $t_{ER}$  after  $V_{CC}$  reaches  $V_{PFD}$  to allow for processor stabilization. After  $t_{ER}$ , normal RAM operation can resume.

For more information on Battery Storage Life refer to the Application Note AN1012.

### POWER SUPPLY DECOUPLING and UNDERSHOOT PROTECTION

$I_{CC}$  transients, including those produced by output switching, can produce voltage fluctuations, resulting in spikes on the  $V_{CC}$  bus. These transients can be reduced if capacitors are used to store energy, which stabilizes the  $V_{CC}$  bus. The energy stored in the bypass capacitors will be released as low going spikes are generated or energy will be absorbed when overshoots occur. A ceramic bypass capacitor value of 0.1µF (as shown in Figure 11) is recommended in order to provide the needed filtering.

In addition to transients that are caused by normal SRAM operation, power cycling can generate negative voltage spikes on  $V_{CC}$  that drive it to values below  $V_{SS}$  by as much as one Volt. These negative spikes can cause data corruption in the SRAM while in battery backup mode. To protect from these voltage spikes, it is recommended to connect a schottky diode from  $V_{CC}$  to  $V_{SS}$  (cathode connected to  $V_{CC}$ , anode to  $V_{SS}$ ). Schottky diode 1N5817 is recommended for through hole and MBRS120T3 is recommended for surface mount.

**Table 12. Ordering Information Scheme**

Example:

	M48Z512AY	-85	PM	1
<b>Device Type</b>				
M48Z				
<b>Supply Voltage and Write Protect Voltage</b>				
512A = $V_{CC} = 4.75V$ to $5.5V$ ; $V_{PFD} = 4.5V$ to $4.75V$				
512AY = $V_{CC} = 4.5V$ to $5.5V$ ; $V_{PFD} = 4.2V$ to $4.5V$				
512AV = $V_{CC} = 3.0V$ to $3.6V$ ; $V_{PFD} = 2.8V$ to $3.0V$				
<b>Speed</b>				
-70 = 70ns				
-85 = 85ns				
<b>Package</b>				
PM = PMDIP32				
CS <sup>(1)</sup> = Surface Mount Chip Set solution M40Z300/W (SOH28) + M68Z512/W (TSOP II 32)				
<b>Temperature Range</b>				
1 = 0 to 70 °C				
9 <sup>(2)</sup> = Extended Temperature				

Note: 1. The SOIC package (SOH28) requires the battery package (SNAPHAT) which is ordered separately under the part number "M4Z32-BR00SH1" in plastic tube or "M4Z32-BR00SH1TR" in Tape & Reel form.  
 2. Contact Sales Offices for availability of Extended Temperature.

**Caution:** Do not place the SNAPHAT battery package "M4Z32-BR00SH1" in conductive foam since this will drain the lithium button-cell battery.

For a list of available options (Speed, Package, etc...) or for further information on any aspect of this device, please contact the STMicroelectronics Sales Office nearest to you.

**Table 13. Revision History**

Date	Revision Details
March 2000	First Issue
07/19/00	M48Z12AV added

Table 14. TSOP II 32 - 32 lead Plastic Thin Small Outline II, 10 x 20 mm, Package Mechanical Data

Symbol	millimeters			inches		
	Typ	Min	Max	Typ	Min	Max
A			1.20			0.047
A1		0.05	0.15		0.002	0.006
A2		0.95	1.05		0.037	0.041
b		0.30	0.52		0.012	0.020
C		0.12	0.21		0.005	0.008
D		20.82	21.08		0.820	0.830
e	1.27	–	–	0.050	–	–
E		11.56	11.96		0.455	0.471
E1		10.03	10.29		0.395	0.405
L		0.40	0.60		0.016	0.024
$\alpha$		0°	5°		0°	5°
CP			0.10			0.004

Figure 12. TSOP II 32 - 32 lead Plastic Thin Small Outline II, 10 x 20 mm, Package Outline

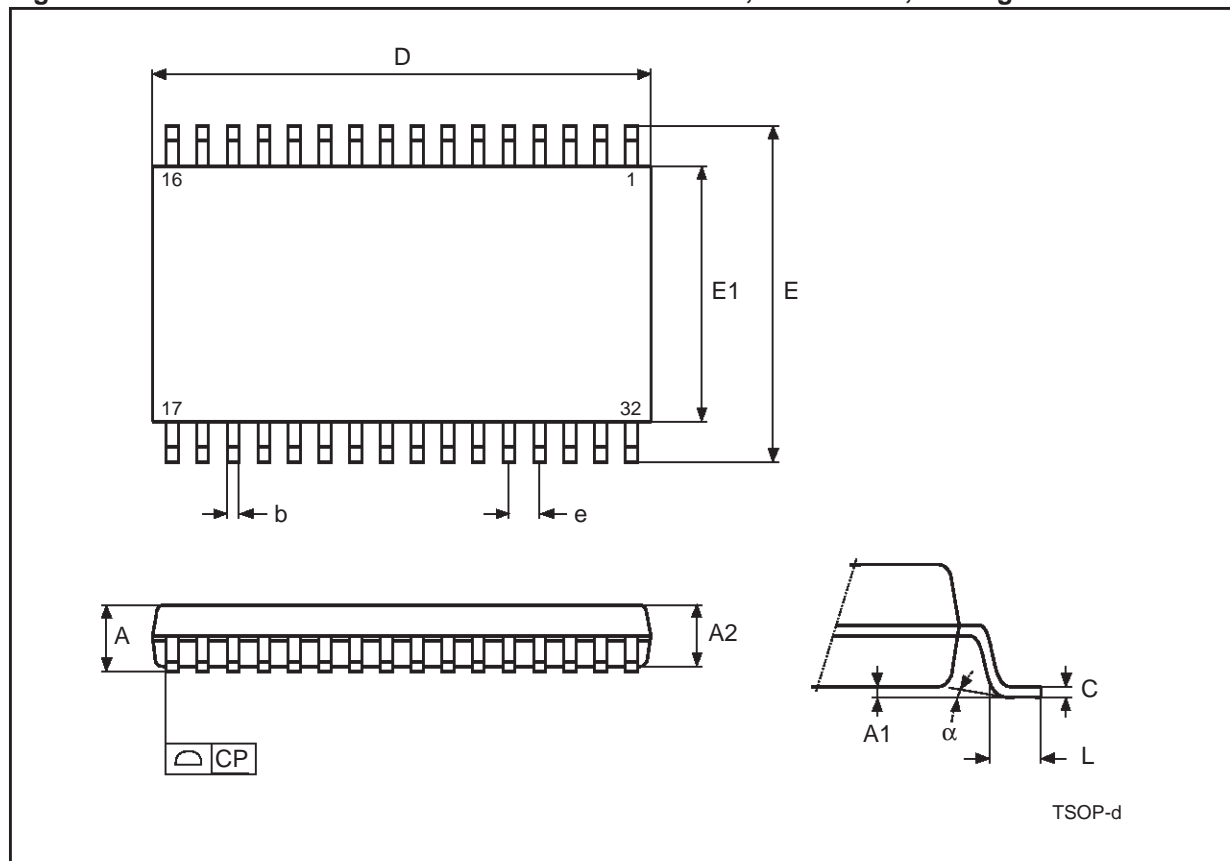
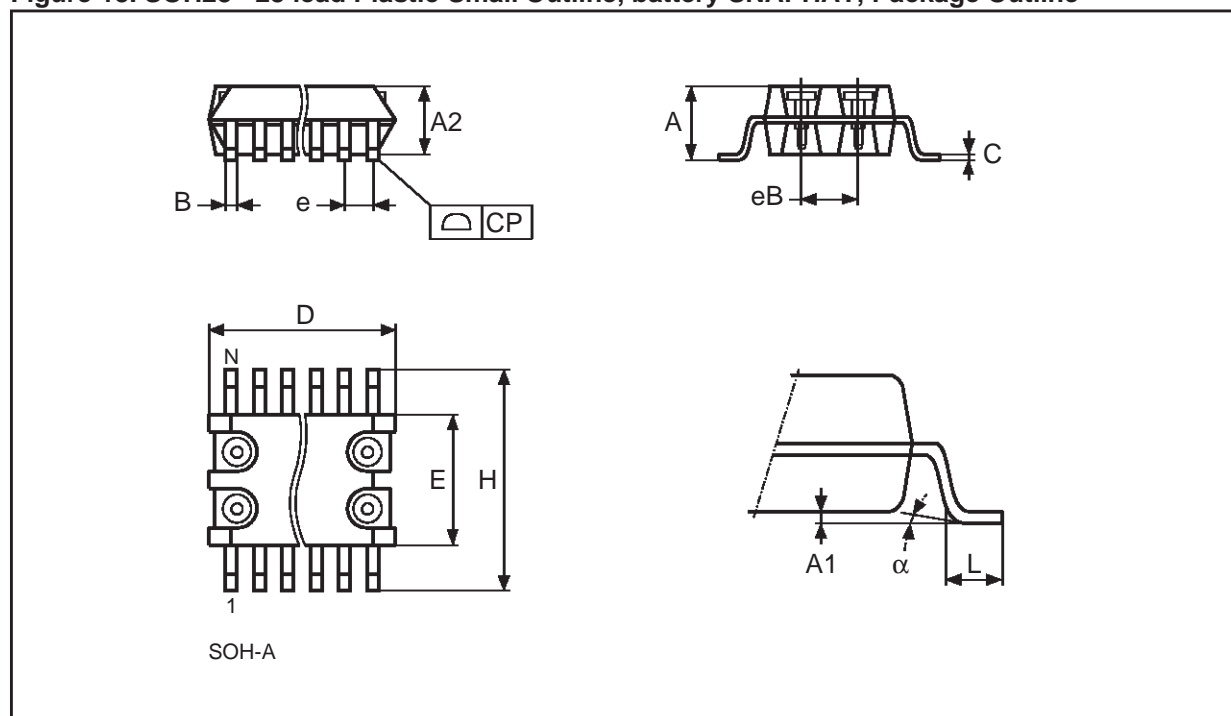


Table 15. SOH28 - 28 lead Plastic Small Outline, battery SNAPHAT, Package Mechanical Data

Symbol	millimeters			inches		
	Typ	Min	Max	Typ	Min	Max
A			3.05			0.120
A1		0.05	0.36		0.002	0.014
A2		2.34	2.69		0.092	0.106
B		0.36	0.51		0.014	0.020
C		0.15	0.32		0.006	0.012
D		17.71	18.49		0.697	0.728
E		8.23	8.89		0.324	0.350
e	1.27	–	–	0.050	–	–
eB		3.20	3.61		0.126	0.142
H		11.51	12.70		0.453	0.500
L		0.41	1.27		0.016	0.050
$\alpha$		0°	8°		0°	8°
N	28			28		
CP			0.10			0.004

Figure 13. SOH28 - 28 lead Plastic Small Outline, battery SNAPHAT, Package Outline



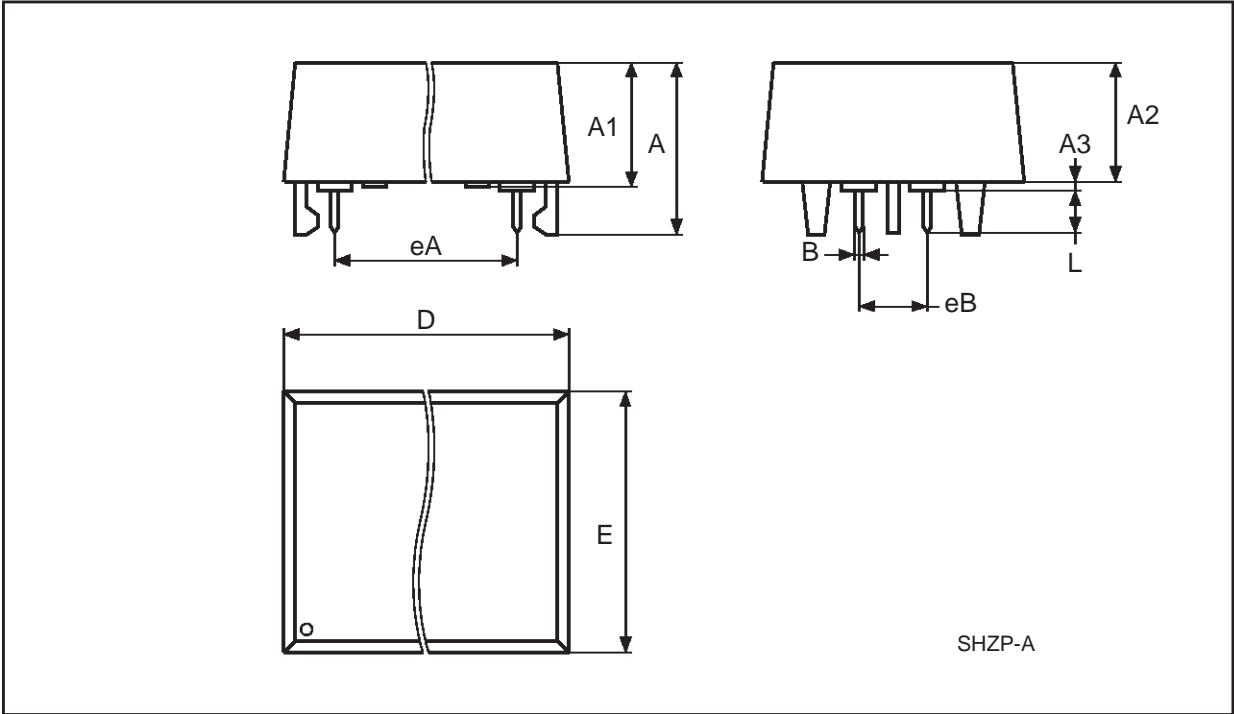
Drawing is not to scale.

M48Z512A, M48Z512AY, M48Z512AV

Table 16. M4Z32-BR00SH SNAPHAT Housing for 120 mAh Battery, Package Mechanical Data

Symbol	millimeters			inches		
	Typ	Min	Max	Typ	Min	Max
A			10.54			0.415
A1		8.00	8.51		0.315	0.335
A2		7.24	8.00		0.285	0.315
A3			0.38			0.015
B		0.46	0.56		0.018	0.022
D		21.21	21.84		0.835	0.860
E		17.27	18.03		0.680	0.710
eA		15.55	15.95		0.612	0.628
eB		3.20	3.61		0.126	0.142
L		2.03	2.29		0.080	0.090

Figure 14. M4Z32-BR00SH SNAPHAT Housing for 120 mAh Battery, Package Outline



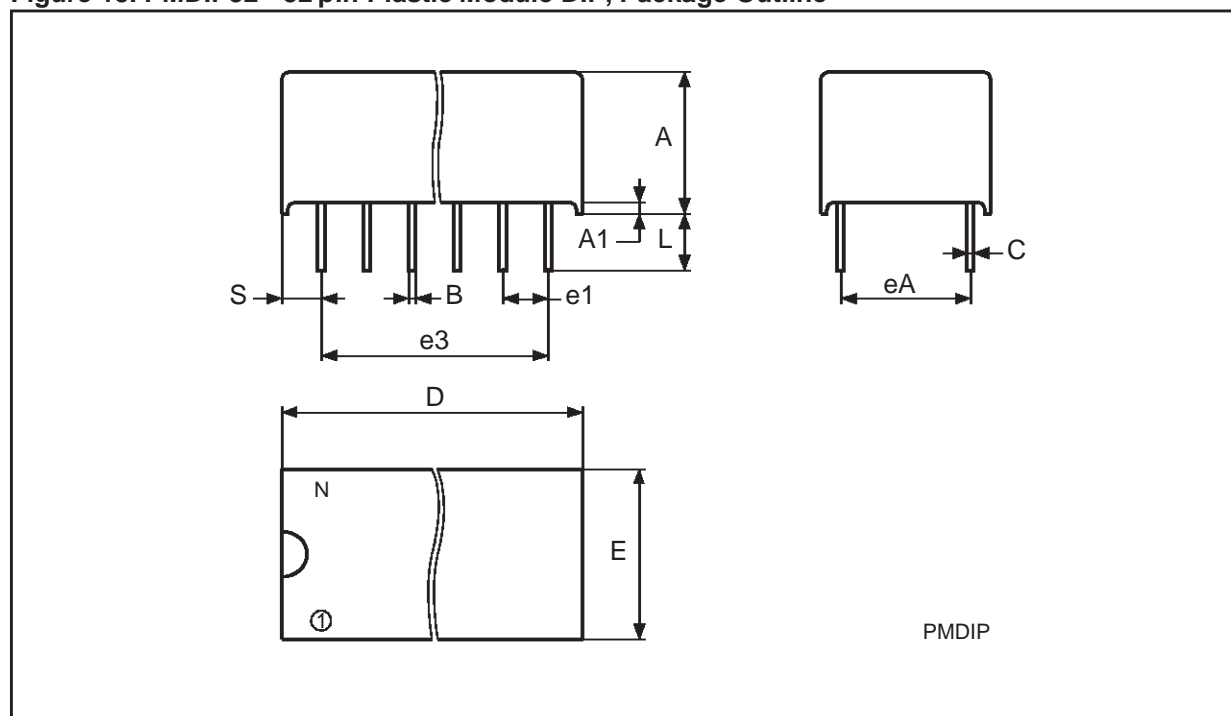
Drawing is not to scale.



Table 17. PMDIP32 - 32 pin Plastic Module DIP, Package Mechanical Data

Symbol	millimeters			inches		
	Typ	Min	Max	Typ	Min	Max
A		9.27	9.52		0.365	0.375
A1		0.38	–		0.015	–
B		0.43	0.59		0.017	0.023
C		0.20	0.33		0.008	0.013
D		42.42	43.18		1.670	1.700
E		18.03	18.80		0.710	0.740
e1		2.29	2.79		0.090	0.110
e3		34.29	41.91		1.350	1.650
eA		14.99	16.00		0.590	0.630
L		3.05	3.81		0.120	0.150
S		1.91	2.79		0.075	0.110
N		32			32	

Figure 15. PMDIP32 - 32 pin Plastic Module DIP, Package Outline



Drawing is not to scale.

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